a memory cell array, which are divided into blocks respectively corresponding to said input/output terminals such that only one of the blocks corresponds to a given one of said input/output terminals;

sense amplifiers, which are connected to the blocks at a side thereof, and amplify data of said memory cell array;

switches which are respectively connected to said sense amplifiers; and

signal lines, which connect said sense amplifiers to a corresponding one of said input/output terminals via the switches, wherein said memory cell array includes flash memory cells, wherein data of said memory cell array is erased by one unit of erasure, wherein more than one but not all of said blocks are put together to form the unit of erasure.

7. (Amended) A semiconductor memory device which allows data of a plurality of pages to be read from a memory cell array and stored in sense amplifiers, and allows data of a selected page to be read from the sense amplifiers and output to an exterior of said semiconductor memory device, comprising:

memory cell areas storing data to be input from and output to one common input/output terminal, said memory cell areas respectively corresponding to the plurality of pages and provided adjacent to each other, wherein the sense amplifiers corresponding to said memory cell areas are arranged adjacent to each other; and

signal lines which connect the sense amplifiers corresponding to said memory cell areas to the common input/output terminal, wherein the memory cell array includes flash

memory cells, wherein data of said memory cell array is erased by one unit of erasure, wherein the unit of erasure is formed by putting together the memory cell areas for more than one but not all of input/output terminals.

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A marked-up version of the amended claims is enclosed as required by 37 C.F.R. § 1.121.

Please add new claims 13-16 as follows:

13. (New) The semiconductor memory device as claimed in claim 4, wherein each said unit of erasure is provided with a dedicated word-line driver.

14. (New) The semiconductor memory device as claimed in claim 13, wherein voltages necessary for erasure operation are generated by pump circuits, and said unit of erasure has a size commensurate with the capacity of the pump circuits.

15. (New) The semiconductor memory device as claimed in claim 7, wherein each said unit of erasure is provided with a dedicated word-line driver.

16. (New) The semiconductor memory device as claimed in claim 15, wherein voltages necessary for erasure operation are generated by pump circuits, and said unit of erasure has a size commensurate with the capacity of the pump circuits.